11-15-02

RCE/1700

Honeywell's Docket No. 30-4790 (4780)
Practitioner's Docket No. 100595.0048US3

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Zhang, et al.

Application No.: 09/357,264 Group No.: 1765
Filed: July 19, 1999 Examiner: Charlotte A. Brown
For: Composition for Chemical Mechanical Planarization of Copper, Tantalum and Tantalum Nitride

Box RCE
Assistant Commissioner for Patents
Washington, D.C. 20231

REQUEST FOR CONTINUED EXAMINATION (RCE)
(37 C.F.R. 1.114)

1. Applicant hereby requests continued examination, in accordance with 37 C.F.R. Section 1.114, for the above identified application.

CERTIFICATION UNDER 37 C.F.R. SECTIONS 1.8(a) AND 1.10
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37 C.F.R. Section 1.8(a)

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Date: November 13, 2002

Kristin J. Azcona

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02 FC:1202 90.00 OP

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

WASHINGTON, D.C. 20231

Inventor: **Zhang et al.**	Examiner: Brown, Charlotte A.
Serial No: **09/357264**	Art Unit: 1765
Filed: **July 19, 1999**	
For: **Comp. for Chemical Mechanical Planarization of Copper, Tantalum and Tantalum Nitride**	

PRELIMINARY AMENDMENT

The Honorable Commissioner
of Patents and Trademarks
Washington, D.C. 20231

Dear Sir:

IN THE CLAIMS

19. A method of accomplishing chemical mechanical planarization of a Cu/Ta/TaN surface comprising:

providing a single-step slurry solution including a combination selected from the group consisting of (i) H_2O_2 with H_3PO_4, H_2SO_4, HNO_3, oxalic acid, acetic acid, or organic acid, (ii) HNO_3 with H_3PO_4, or H_2SO_4; and (iii) an oxidizing reagent with HF;

applying the solution to the surface; and

planarizing both the Cu and at least one of the Ta and TaN during a single processing step.